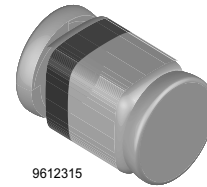


## Small Signal Fast Switching Diode

### Features

- Silicon Epitaxial Planar Diodes
- Electrical data identical with the device 1N4151
- Micro Melf package
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### Applications

- Extreme fast switches

### Mechanical Data

**Case:** MicroMELF Glass case

**Weight:** approx. 12 mg

**Cathode Band Color:** Black

**Packaging Codes/Options:**

TR3 / 10 k per 13" reel (8 mm tape), 10 k/box

TR / 2.5 k per 7" reel (8 mm tape), 12.5 k/box

### Parts Table

Part	Type differentiation	Ordering code	Remarks
MCL4151	$V_{RRM} = 75\text{ V}$	MCL4151-TR3 or MCL4151-TR	Tape and Reel

### Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		$V_{RRM}$	75	V
Reverse voltage		$V_R$	50	V
Peak forward surge current	$t_p = 1\text{ }\mu\text{s}$	$I_{FSM}$	2	A
Repetitive peak forward current		$I_{FRM}$	450	mA
Forward continuous current		$I_F$	200	mA
Average forward current	$V_R = 0$	$I_{FAV}$	150	mA
Power dissipation		$P_V$	500	mW



### Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction to ambient air	mounted on epoxy-glass hard tissue, Fig. 4, 35 $\mu\text{m}$ copper clad, 0.9 $\text{mm}^2$ copper area per electrode	$R_{thJA}$	500	K/W
Junction temperature		$T_j$	175	$^{\circ}\text{C}$
Storage temperature range		$T_{stg}$	- 65 to + 175	$^{\circ}\text{C}$

### Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 50\text{ mA}$	$V_F$		880	1000	mV
Reverse voltage	$V_R = 50\text{ V}$	$I_R$			50	nA
	$V_R = 50\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	$I_R$			50	$\mu\text{A}$
Breakdown voltage	$I_R = 5\text{ }\mu\text{A}, t_p/T = 0.01, t_p = 0.3\text{ ms}$	$V_{(BR)}$	75			V
Diode capacitance	$V_R = 0, f = 1\text{ MHz}, V_{HF} = 50\text{ mV}$	$C_D$			2	pF
Reverse recovery time	$I_F = I_R = 10\text{ mA}, i_R = 1\text{ mA}$	$t_{rr}$			4	ns
	$I_F = 10\text{ mA}, V_R = 6\text{ V}, i_R = 0.1 \times I_R, R_L = 100\text{ }\Omega$	$t_{rr}$			2	ns

### Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

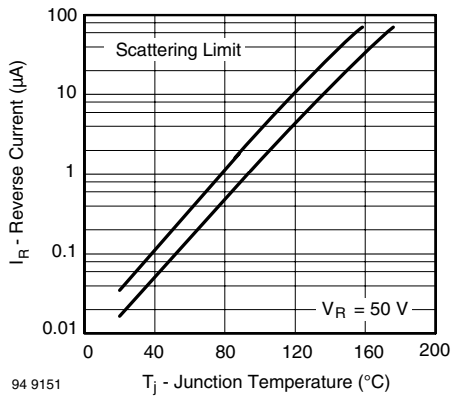


Figure 1. Reverse Current vs. Junction Temperature

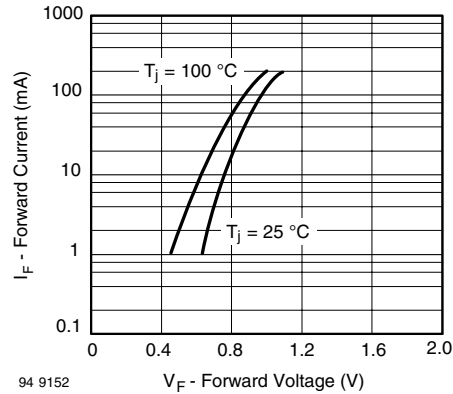


Figure 2. Forward Current vs. Forward Voltage

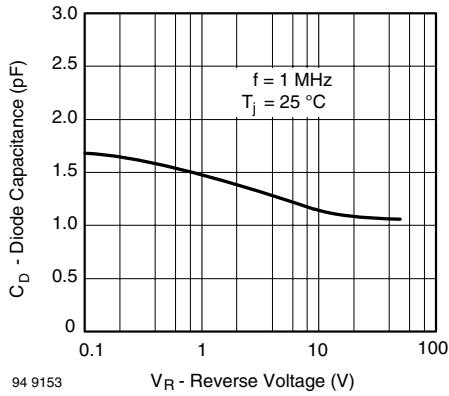


Figure 3. Diode Capacitance vs. Reverse Voltage

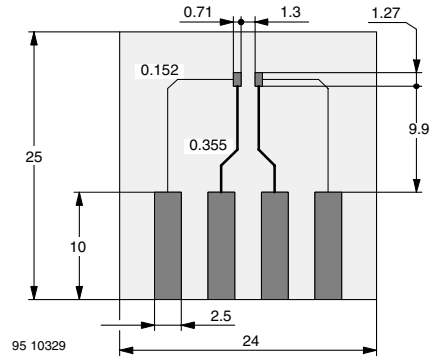
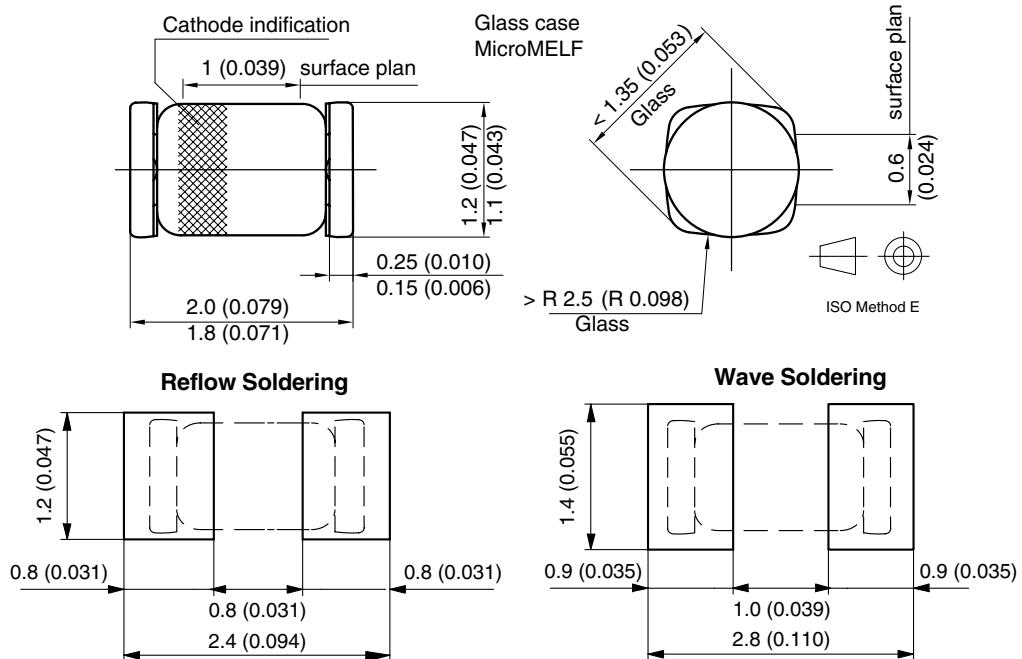


Figure 4. Board for  $R_{thJA}$  definition (in mm)

## Package Dimensions in mm (Inches)



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### Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design  
and may do so without further notice.

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Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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